

TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

MT6C04AE

VHF~UHF Band Low Noise Amplifier Applications

- Two devices are built in to the super-thin and extreme super mini (6 pins) package: ES6

Mounted Devices

	Q1/Q2: SSM (TESM)
Three-pins (SSM/TESM) mold products are corresponded.	MT3S04AS (MT3S04AT)

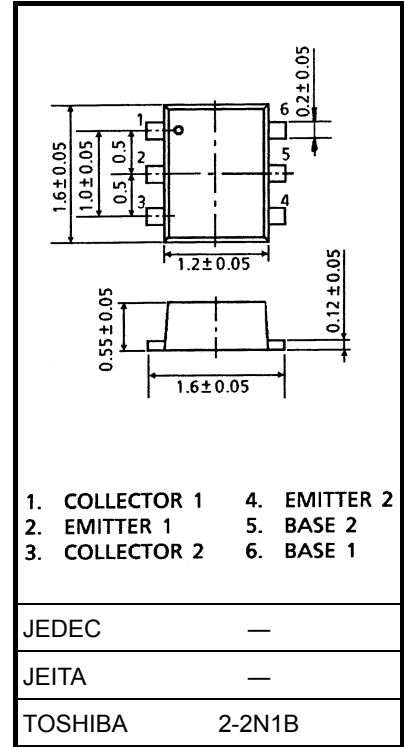
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Q1/Q2	Unit
Collector-base voltage	V _{CBO}	10	V
Collector-emitter voltage	V _{CEO}	5	V
Emitter-base voltage	V _{EBO}	2	V
Collector current	I _C	40	mA
Base current	I _B	10	mA
Collector power dissipation	P _C (Note 1)	100	mW
Junction temperature	T _j	125	°C
Storage temperature range	T _{stg}	-55~125	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

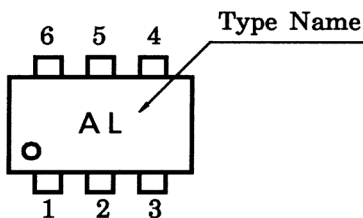
Note 1: Total power dissipation of Q1 and Q2.

Unit: mm

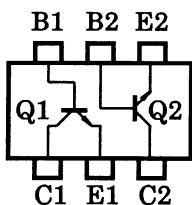


Weight: 0.003 g (typ.)

Marking



Pin Assignment (top view)



Electrical Characteristics Q1/Q2 (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 5\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 1\text{ V}, I_C = 0$	—	—	1	μA
DC current gain	h_{FE}	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	80	—	160	
Transition frequency	$f_T(1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}$	2	4.5	—	GHz
	$f_T(2)$	$V_{CE} = 3\text{ V}, I_C = 7\text{ mA}$	5	7	—	
Insertion gain	$ S_{21e} ^2(1)$	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	—	8.5	—	dB
	$ S_{21e} ^2(2)$	$V_{CE} = 3\text{ V}, I_C = 20\text{ mA}, f = 1\text{ GHz}$	7.5	11	—	
Noise figure	NF (1)	$V_{CE} = 1\text{ V}, I_C = 5\text{ mA}, f = 1\text{ GHz}$	—	1.3	2.2	dB
	NF (2)	$V_{CE} = 3\text{ V}, I_C = 7\text{ mA}, f = 1\text{ GHz}$	—	1.2	2	
Reverse transfer capacitance	C_{re}	$V_{CB} = 1\text{ V}, I_E = 0, f = 1\text{ MHz}$ (Note 2)	—	0.9	1.25	pF

Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

RESTRICTIONS ON PRODUCT USE

20070701-EN GENERAL

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